



YJQ50N04B

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	50A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.5m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	6m
100% EAS Tested	

General Description

Trench Power LV MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$

Applications

High current load applications
Load switching
Hard switched and high frequency circuits
Uninterruptible power supply

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
		V_{GS}	± 20	V
Drain Current	$T_A=25$	I_D	12	A
	$T_A=100$		7.5	
	$T_C=25$			
	$T_C=100$		31	
Pulsed Drain Current ^A		I_{DM}	200	A
Avalanche energy ^B				



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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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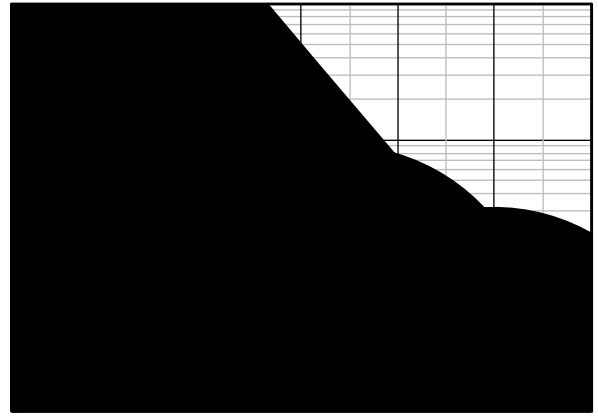
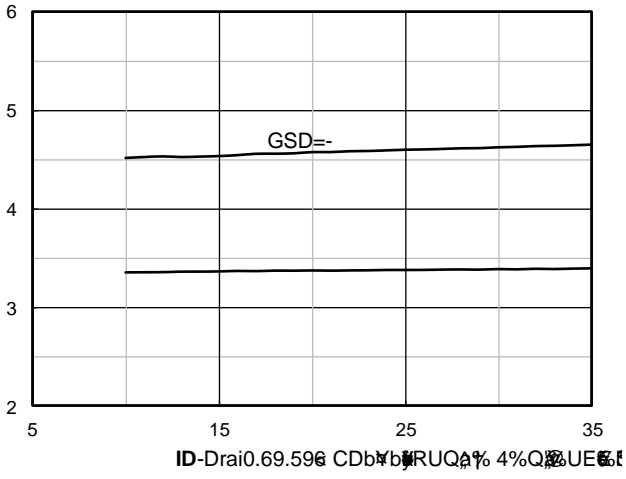
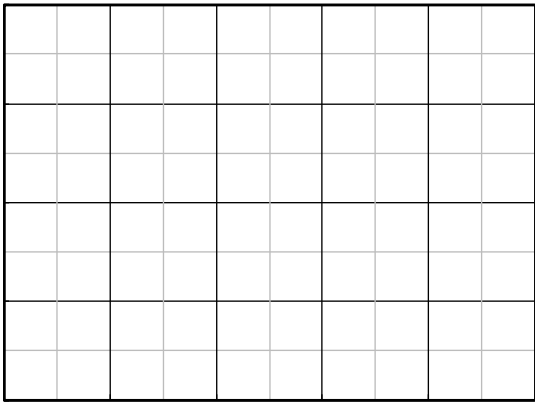


Figure 8. Forward characteristics of reverse diode





DFN3333-8L Package information

